

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP3060EQ uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification. It is ESD protested.

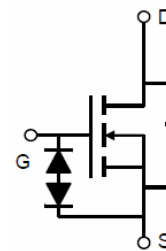
General Features

- $V_{DS}=30V, I_D=60A$
 $R_{DS(ON)}=4m\Omega$ (typical) @ $V_{GS}=10V$
 $R_{DS(ON)}=5.4m\Omega$ (typical) @ $V_{GS}=4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- ESD protection : HBM Class 2

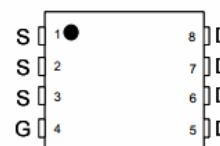
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

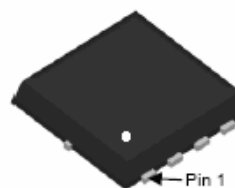
100% UIS TESTED!
100% ΔV_{ds} TESTED!



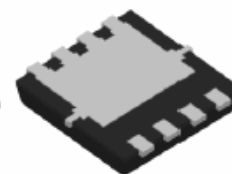
Schematic Diagram



Top View and Pin Assignment



Top View



Bottom View

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP3060EQ	NCEP3060EQ	DFN3.3X3.3-8L	-	-	-

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	60	A
Drain Current-Continuous($T_C=100^{\circ}C$)	$I_D(100^{\circ}C)$	42	A
Pulsed Drain Current (Package Limited)	I_{DM}	200	A
Maximum Power Dissipation	P_D	48	W
Derating factor		0.38	W/ $^{\circ}C$
Single pulse avalanche energy (Note 5)	E_{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.6	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	4	4.3	mΩ
		V _{GS} =4.5V, I _D =30A	-	5.4	6	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =30A		30	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	2200	2640	PF
Output Capacitance	C _{oss}		-	807	906	PF
Reverse Transfer Capacitance	C _{rss}		-	22.7	27	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =30A V _{GS} =10V, R _G =1.6Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	4.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	29	-	nS
Turn-Off Fall Time	t _f		-	8.5	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =30A, V _{GS} =10V	-	34.6	38	nC
Gate-Source Charge	Q _{gs}		-	7.8		nC
Gate-Drain Charge	Q _{gd}		-	3.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =30A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	60	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S di/dt = 500A/μs ^(Note3)	-	16	-	nS
Reverse Recovery Charge	Q _{rr}		-	35	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, L=0.5mH, R_G=25\Omega$

Typical Electrical and Thermal Characteristics

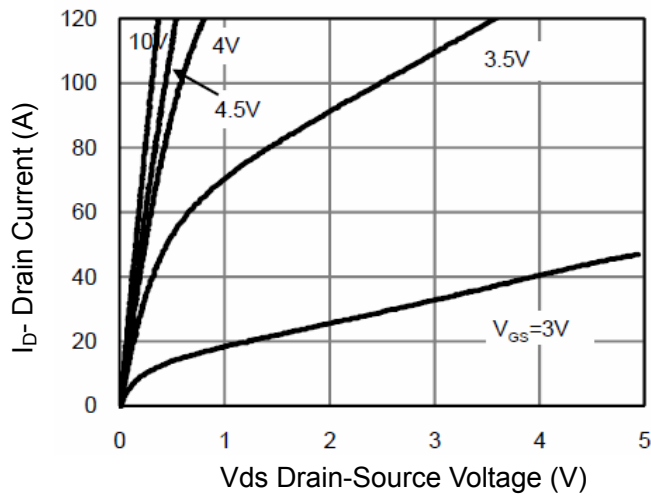


Figure 1 Output Characteristics

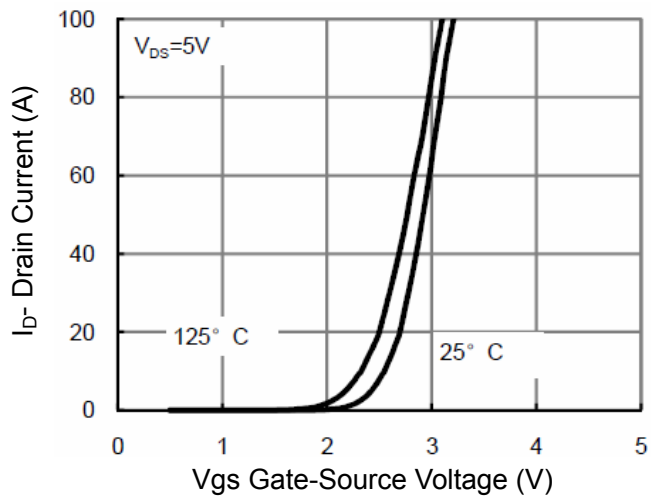


Figure 2 Transfer Characteristics

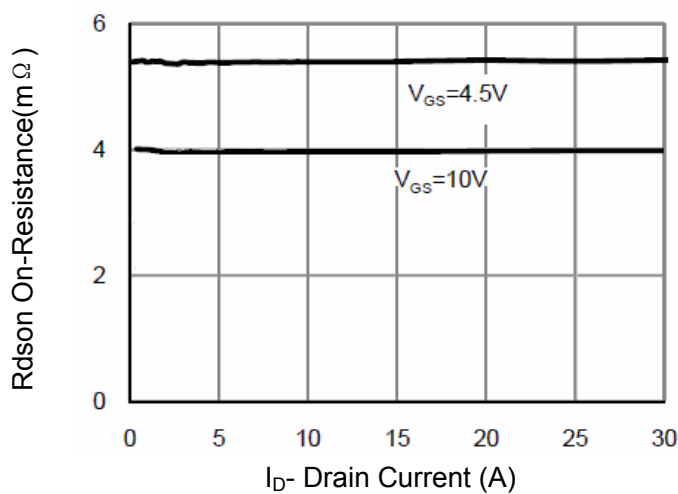


Figure 3 Rdson- Drain Current

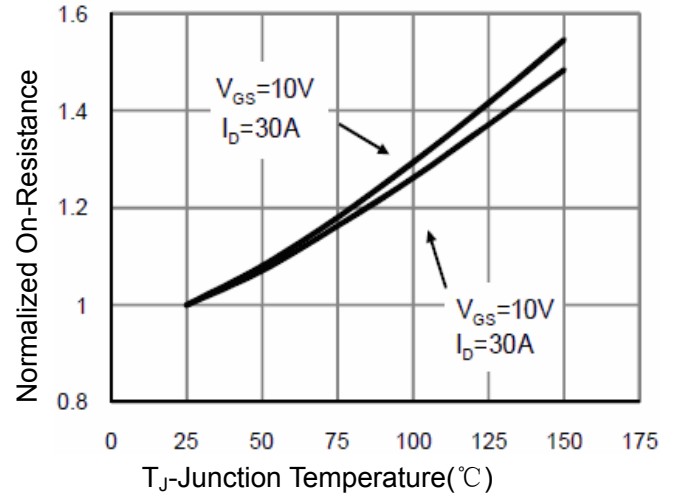


Figure 4 Rdson-Junction Temperature

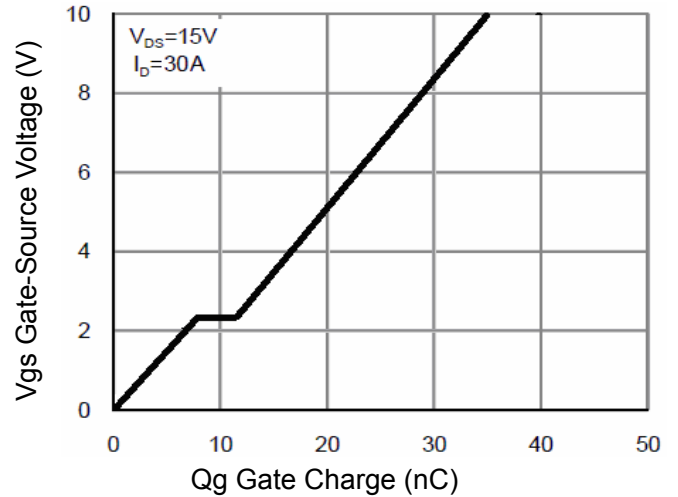


Figure 5 Gate Charge

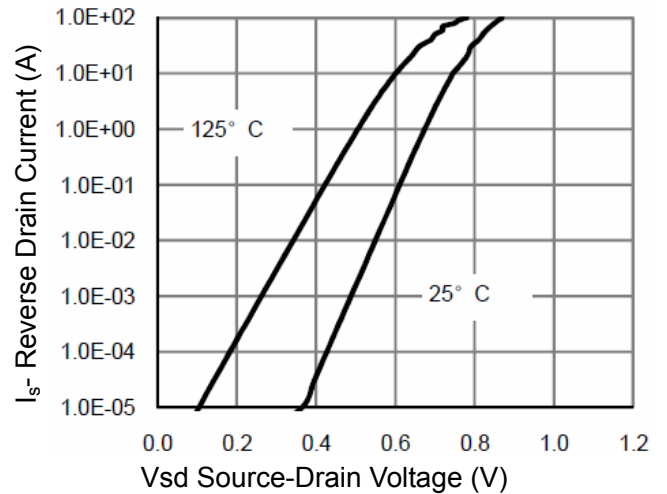


Figure 6 Source- Drain Diode Forward

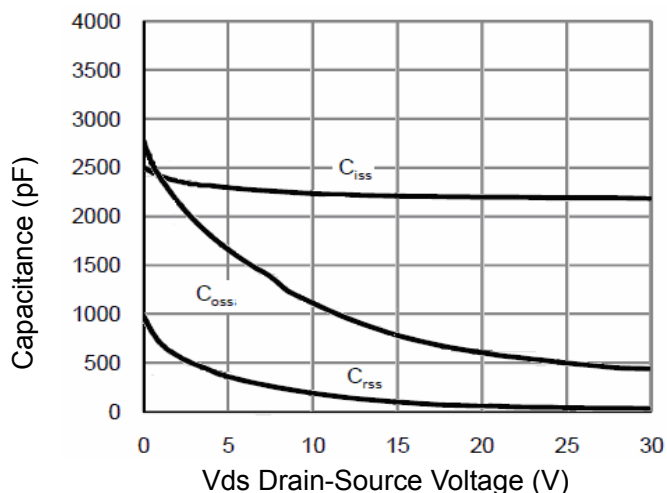


Figure 7 Capacitance vs Vds

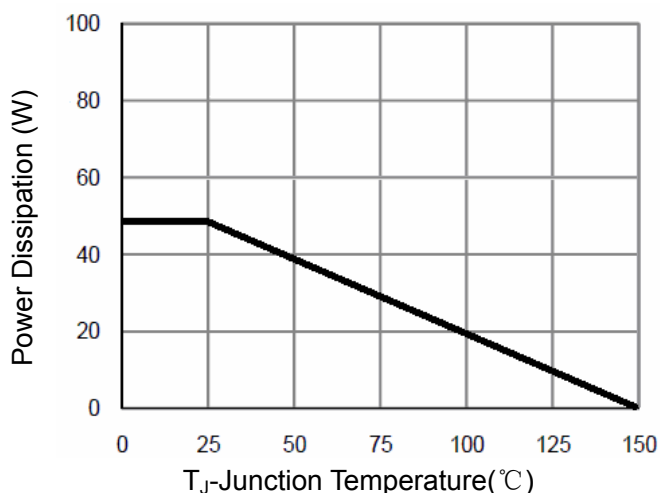


Figure 9 Power De-rating

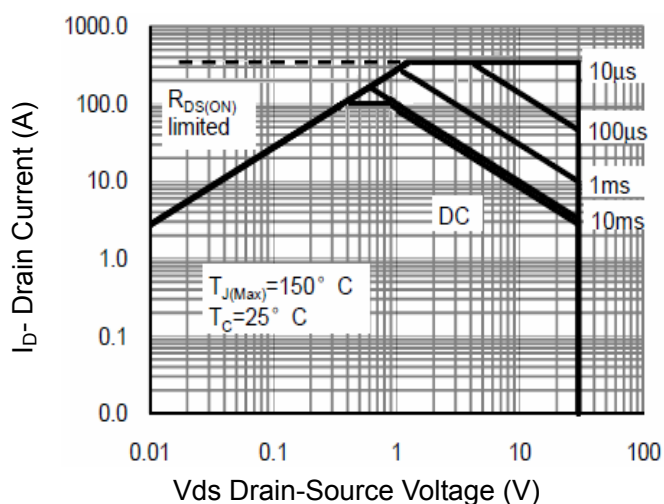


Figure 8 Safe Operation Area

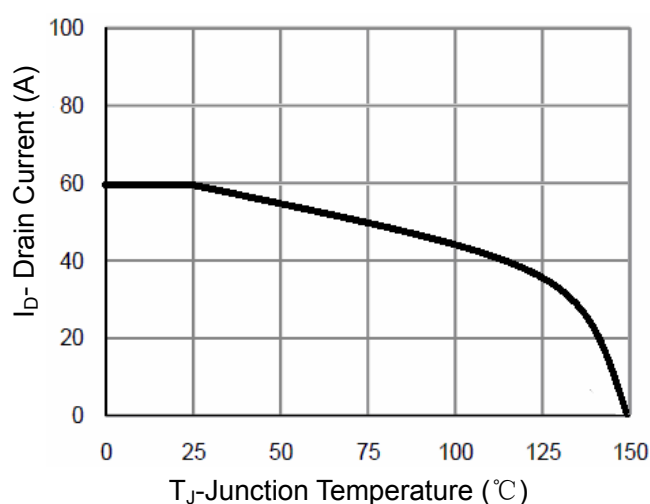


Figure 10 Current De-rating

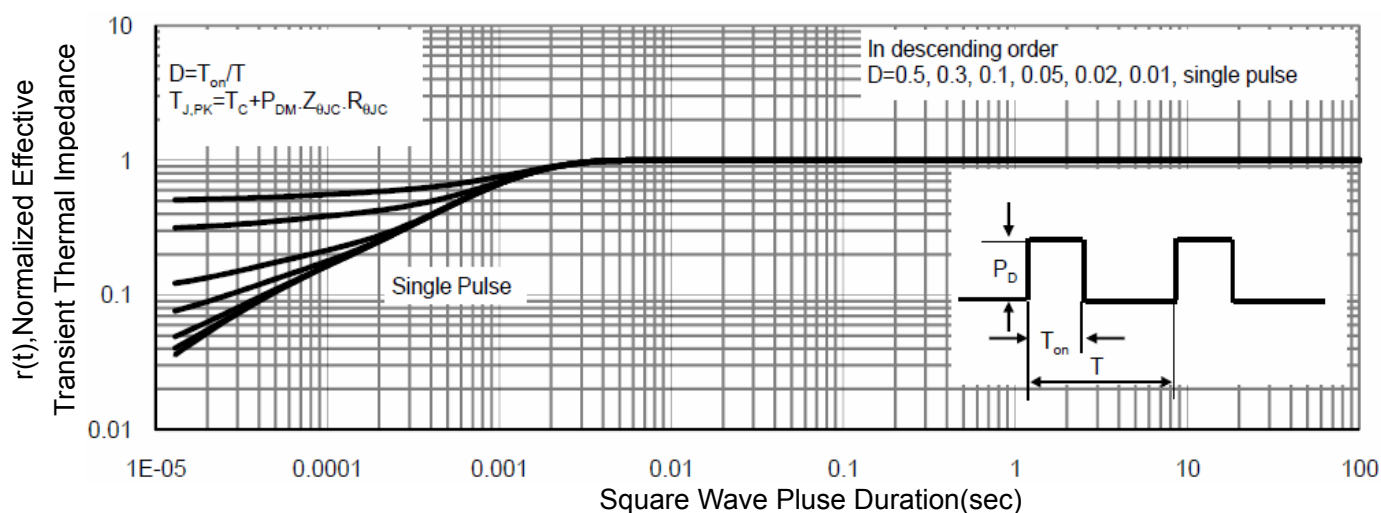
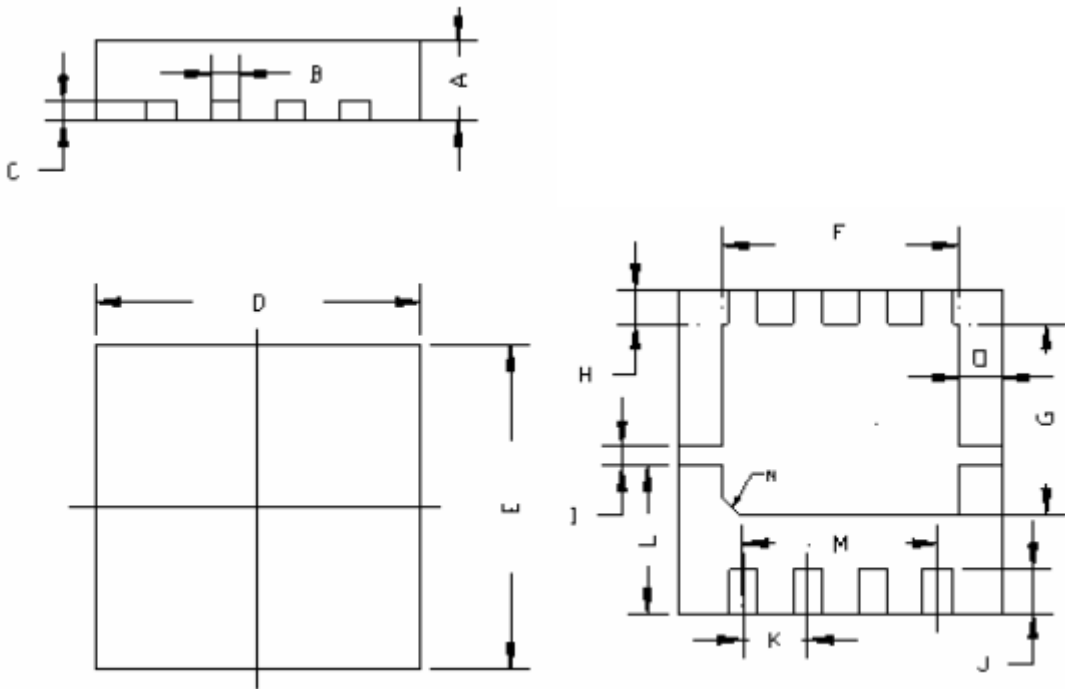


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3.3X3.3-8L Package Information



A	B	C	D
0.8±0.05	0.3±0.05	0.2±0.02	3.25±0.05
E	F	G	H
3.25±0.05	2.35±0.15	1.9±0.1	0.35±0.05
I	J	K	L
0.2±0.05	0.45±0.05	0.65±0.05	1.48±0.1
M	N	O	
1.95±0.15	0.15*45°	0.45±0.05	
单位: mm			

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